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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known

Application Number	Continuation of 10/348,965
Filing Date	Herewith
First Named Inventor	Satoru TAKASE
Group Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	001701.00202

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Number	Kind Code ² (if known)				
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Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ₃
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
MT		JP	4-102295	A	Fujitsu Ltd.	04-03-1992		
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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		Betty Prince, "Semiconductor Memories," 1983, Wiley, 2 nd Ed., pp. 761-762	
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Examiner Signature	MT. TRAN	Date Considered	5/24/03
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¹EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.